



HYBRIS

Enhanced Hybrid Storage Systems

Optimization of the HESS power conversion architecture

Workshop on energy storage and its crucial role in the energy transition with focus on hybrid solutions

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□ 1st HYBRIS Workshop

□ Horcynus Orca Foundation, 23rd June 2022

❑ *HYBRIS WP3 Task 3.3: Optimal electrical architecture of each BESS and the HESS (M9-M17)*

This task aims at achieving the optimal electrical and conversion architecture for hybrid electric storage systems (HESS).

An optimization problem is defined with a search space consisting of commercial passive and active electrical and electronic components.

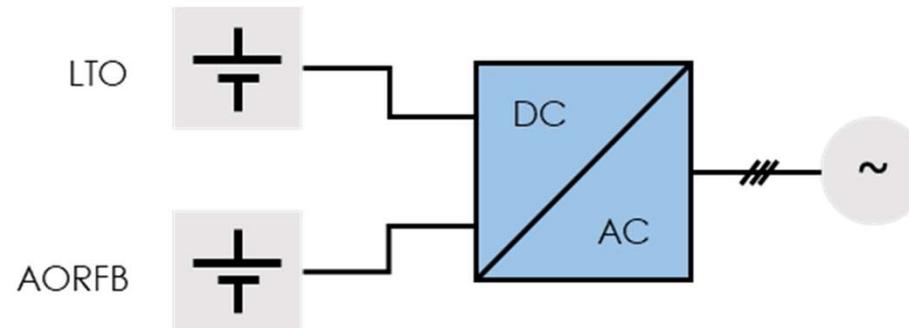
The final target is to define an architecture for the HESS that would ensure the following:

- ❑ **Scalable** and **modular** power system for different ESS integration.
- ❑ Optimized **trade-off** among **efficiency**, **cost**, and **reliability**.

Work performed by IREC with the collaboration of CEA and the support from TOS and KEMI.

Hybrid Electric Storage System

General scheme of the HESS

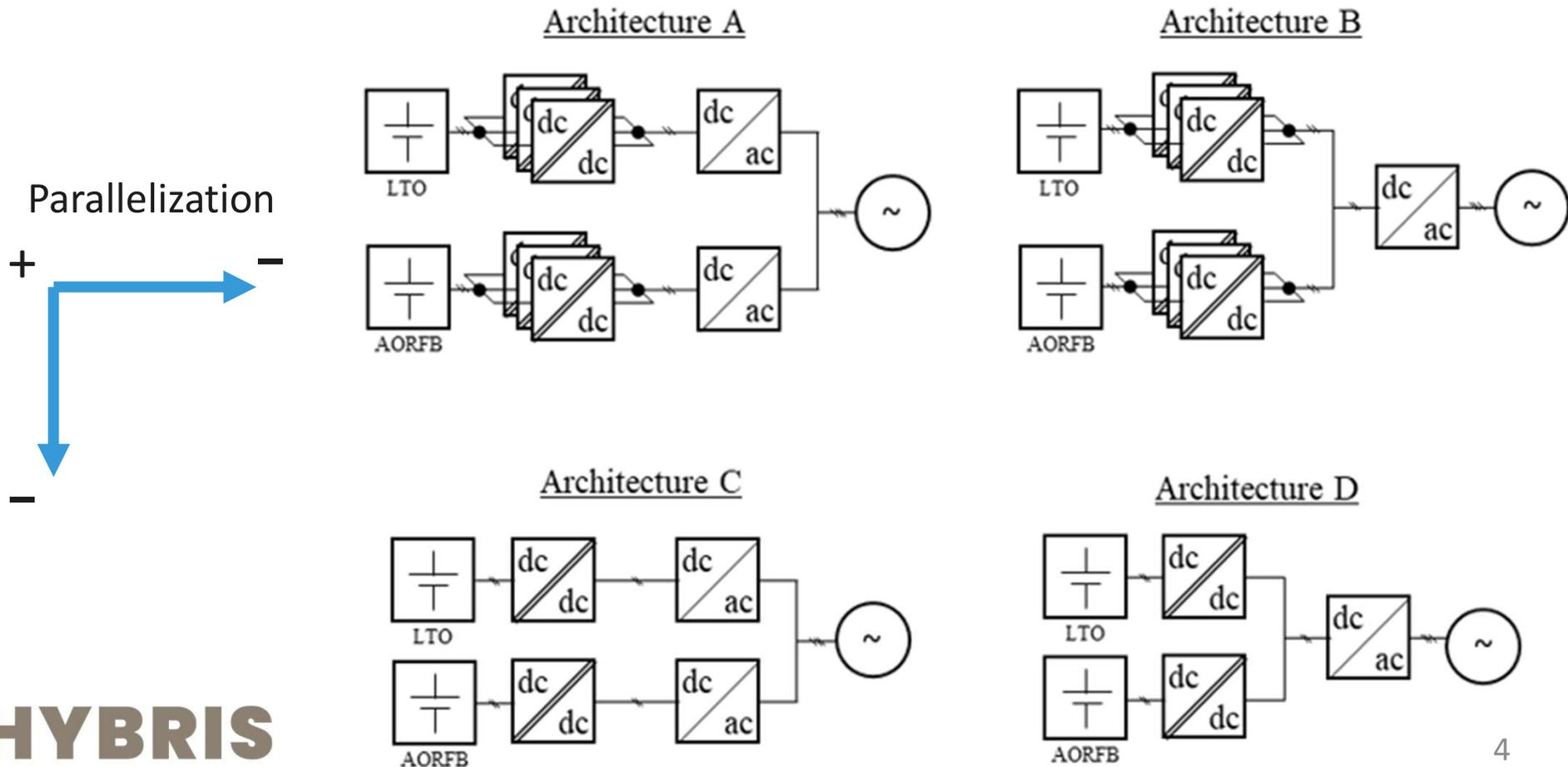


Power conversion system electrical ratings:

Port	dc nom. voltage	dc max. voltage	dc max. current	Nominal power	ac phase-to-phase nom. voltage	ac phase nom. current	ac nom. $\cos(\varphi)$
dc (LTO)	330 V	390 V	200 A	50 kW	-	-	-
dc (AORFB)	50 V	70 V	165 A	9 kW	-	-	-
ac	-	-	-	59 kVA	400 V _{rms} ±10 %	85 A	1

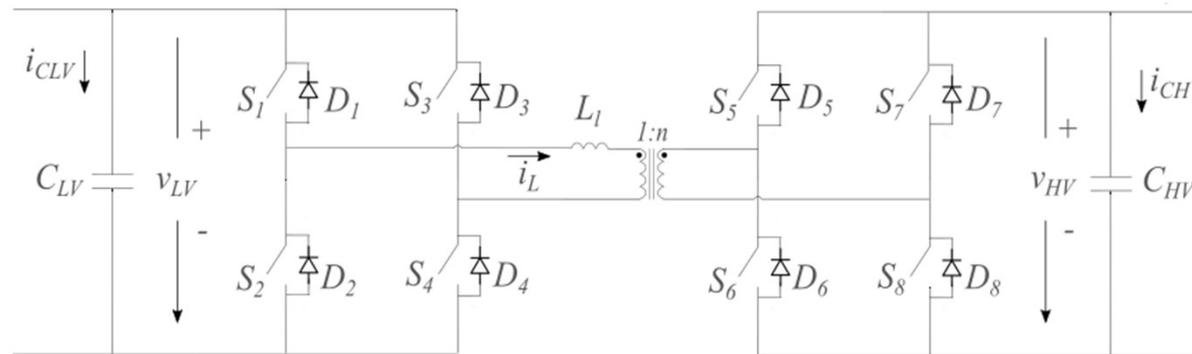
Explored power system architectures

- Four conversion architectures are explored, with different degrees of parallelization.

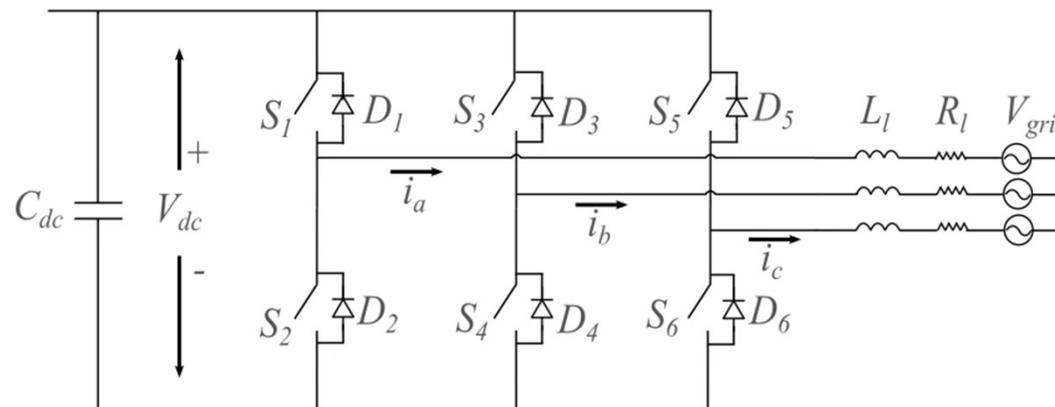


Power converter topologies

- **DC-DC modules:** Dual-active-bridge converter (DAB) employing conventional phase shift modulation.



- **DC-AC modules:** Three-phase inverter employing SPWM.



Multiobjective Optimization Problem

For each architecture ($x \in \{A, B, C, D\}$) a multiobjective optimization problem is defined.

Objective function:

$$G_{x,w}(\mathbf{y}) = W_{\zeta w} \cdot \zeta'_{x,w}(\mathbf{y}) + W_{\sigma w} \cdot \sigma'_{x,w}(\mathbf{y})$$

- $\zeta'_{x,w}$: Conversion losses (in p.u.).
- $\sigma'_{x,w}$: System capital and reliability cost (in p.u.).

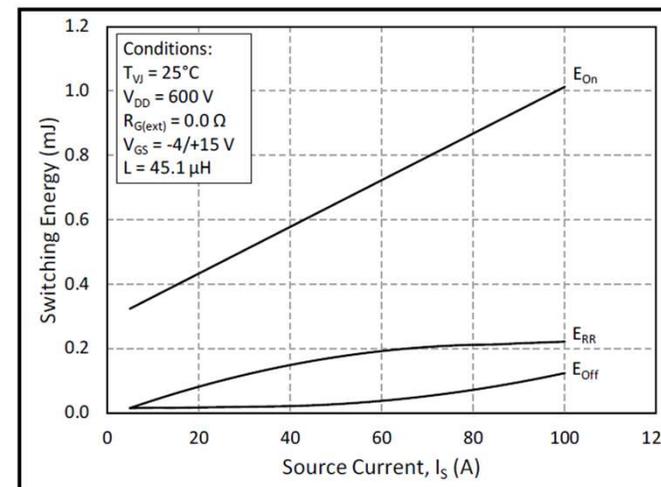
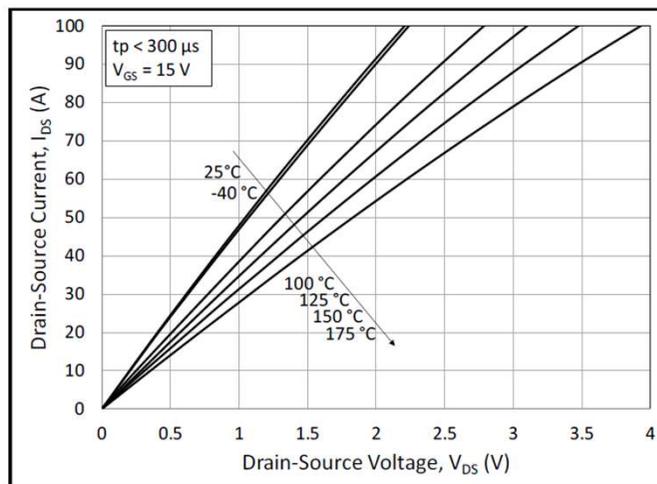
To explore the cost-losses trade-off, weights $W_{\zeta w}$ and $W_{\sigma w}$ are used. Three different weight sets (WS) are defined:

- WS1: $\{W_{\zeta 1}, W_{\sigma 1}\} = \{0.5, 0.5\}$. Losses priority = Cost priority.
- WS2: $\{W_{\zeta 2}, W_{\sigma 2}\} = \{0.2, 0.8\}$. Losses priority > Cost priority.
- WS3: $\{W_{\zeta 3}, W_{\sigma 3}\} = \{0.8, 0.2\}$. Losses priority < Cost priority.

ζ – Conversion Losses Objective

To compute the system losses we employ multiple converter component losses models.

- Semiconductor **conduction losses** and **switching losses**.
 - Modelled with linear equations from the devices datasheet data, taking into account junction temperature.



ζ – Conversion Losses Objective

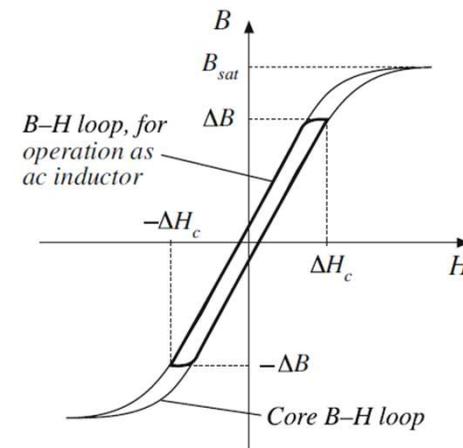
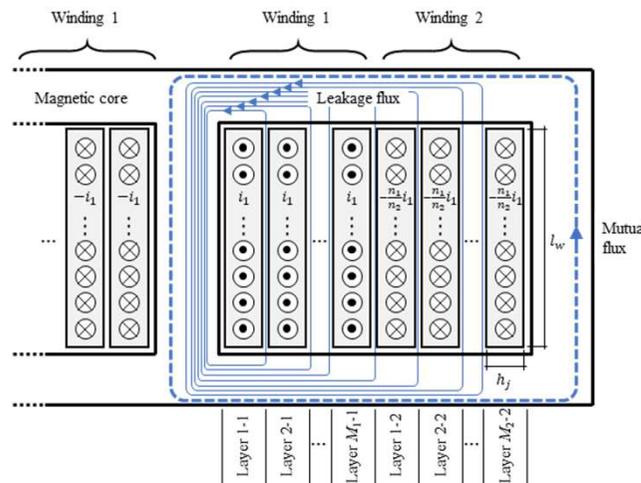
- ❑ Magnetic elements: DAB inductor + transformer and inverter filter inductors.
- ❑ **Copper losses**: dc resistance and ac resistance (skin + proximity effect) in the winding conductors. From simplified Maxwell’s equations [1].

$$P_{dc} = \rho \cdot \frac{n_j \cdot MLT}{npw_j \cdot A_{W,j}} \sum_{j=1}^k I_j^2 \quad | \quad P_{ac,j} = I_{1,j}^2 \cdot R_{dc,j} \cdot \varphi_j \cdot M_j \cdot \left[G_1(\varphi_j) + \frac{2}{3} (M_j^2 - 1) (G_1(\varphi_j) - 2G_2(\varphi_j)) \right]$$

- ❑ **Core losses**: Polynomial regressions from core material datasheets.

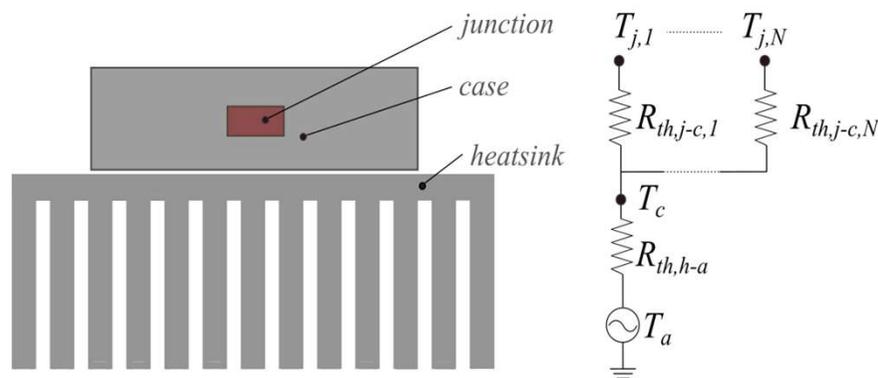
$$P_{Fe} = K_{Fe0} \cdot f_1^\xi \cdot \Delta B^\beta \cdot N_c \cdot A_c \cdot l_m$$

- ❑ **Capacitor losses**: derived from ESR: $P_{cap} = ESR \cdot I_c^2$ (ESR values obtained from the datasheets)



Thermal model

- ❑ We compute the component temperatures since:
 - ❑ **Semiconductor losses = $f(T_j)$.**
 - ❑ **Limit component temperatures** to the maximum specified by the manufacturer.
- ❑ Heat-dissipation thermal models:
 - ❑ **Semiconductors:** Power MOSFETs + body diode attached to heatsink (forced air cooling). Junction temperature (T_j) is computed.
 - ❑ **Magnetics:** Natural convection cooling. Uniform temperature is considered ($T_{\text{magnetic},k}$).
 - ❑ **Capacitors:** Free-standing capacitor with forced air cooling. Capacitor core temperature is computed ($T_{\text{cap},k}$).



- Semiconductors junction temperature

$$T_{j,n} = T_c + R_{th,j-c,n} \cdot (P_{\text{cond},n} + P_{\text{sw},n})$$

- Magnetic elements temperature

$$T_{\text{magnetic},k} = T_{\text{amb}} + \left(\frac{P_{\text{core},k} + P_{\text{copper},k}}{10 \cdot S_{\text{magnetic},k}} \right)^{0.833}$$

- Capacitor core temperature

$$T_{\text{cap}} = T_{\text{amb},k} + (R_{th,cap,0} + R_{th,cap,1}(u_{\text{wind}})) \cdot P_{\text{cap}}$$

σ – Converter Cost Objective

The system cost is divided in two parts:

- ❑ **Capital cost:** Sum of the components acquisition cost. Obtained from cost models [2], [3], [4].
 - ❑ Semiconductor cost = $f(\text{Chip area} + \text{Package})$
 - ❑ Magnetics cost = $f(\text{Core weight} + \text{Copper weight} + \text{Labor cost})$
 - ❑ Capacitors cost = $f(\text{Voltage rating} + \text{Capacitance rating})$
 - ❑ Heatsink cost = $f(\text{HS volume} + \text{fixed cost})$
 - ❑ Fan cost = $f(\text{Fan volume} + \text{fixed cost})$
 - ❑ Auxiliary elements cost = $f(\#\text{Gate drivers} + \#\text{sensors})$

Semiconductor chip area cost [€/mm ²]			
Voltage rating \ SC type	Si PiN Diode	Si MOSFET	SiC MOSFET
1200 V	$4.46 \cdot 10^{-2}$	-	$72 \cdot 10^{-2}$
600 V	$2.46 \cdot 10^{-2}$	$4.48 \cdot 10^{-2}$	$64.8 \cdot 10^{-2}$
100 V	-	$13.24 \cdot 10^{-2}$	-

Semiconductor package cost [€]			
Package type	TO-247-3	SOT 227	Module (variable)
Value	0.55	8.10	$0.52 \cdot A_{\text{mod}} - 4.8$

Magnetic core cost [€/kg]			
Core material	Ferrite	Powder Core	Amorphous
Value	7.5	10.2	14.1

Winding cost [€/kg]			
Conductor type	Round	Litz	Foil
Value	10	10.2	20

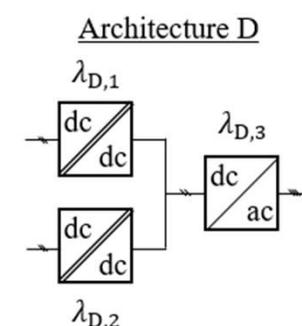
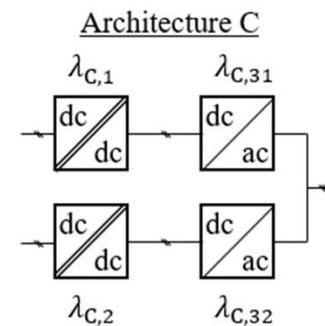
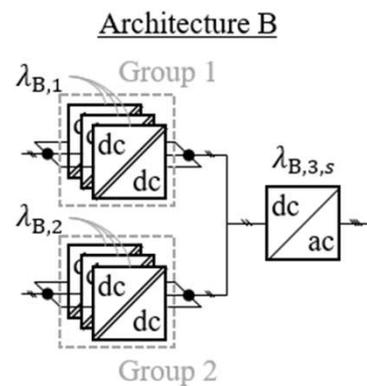
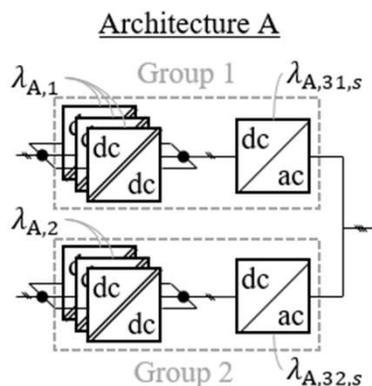
[2] R. Burkart and J. W. Kolar, "Component cost models for multi-objective optimizations of switched-mode power converters," in 2013 IEEE Energy Conversion Congress and Exposition, Sep. 2013, pp. 2139–2146.

[3] R. M. Burkart and J. W. Kolar, "Comparative η - ρ - σ Pareto Optimization of Si and SiC Multi-Level Dual Active Bridge Topologies with Wide Input Voltage Range," IEEE Trans. Power Electron., pp. 1–1, 2016.

[4] R. M. Burkart and J. W. Kolar, "Comparative Life Cycle Cost Analysis of Si and SiC PV Converter Systems Based on Advanced η - ρ - σ Multiobjective Optimization Techniques," IEEE Transactions on Power Electronics, vol. 32, no. 6, pp. 4344–4358, Jun. 2017.

σ - Converter Cost Objective

- ❑ **Reliability cost** = Cost of reparation + Energy revenue lost
 - ❑ Reparation of failed power modules = $f(\text{Probability of modules failure} + \text{Reparation cost})$
 - ❑ Revenue lost from partial/complete shutdown = $f(\text{Probability of modules failure} + \text{Power lost} + \text{Price of energy})$
 - ❑ Computed for a 1-year period (demo-site testing period).
- ❑ **Reliability model:**
 - ❑ Based on Markov chains.
 - ❑ Allows computing the probability of failure of a power module.
 - ❑ Failure rate of the modules = $f(\text{Component temperatures} \ \& \ \text{blocking voltages})$
 - ❑ Architectures A & B can continue operation if one dc-dc module per group fails \rightarrow Partial shutdown.
 - ❑ Architectures C & D must stop operation if any power module fails \rightarrow Complete shutdown.



Optimization variables

$n_{\text{par,sw,DAB,bat},b}$	$L_{\text{HS,DAB,bat},b}$	$type_{\text{wire,L,DAB},b}$
$n_{\text{par,sw,DAB,grid},b}$	$L_{\text{HS,DAB,grid},b}$	$type_{\text{wire,Tx,DAB},b}$
$n_{\text{par,sw,inv},b}$	$L_{\text{HS,inv},b}$	$type_{\text{wire,L,inv},b}$
$type_{\text{sw,DAB,bat,LTO}}$	$n_{\text{par,cap,dclink},b}$	$model_{\text{wire,L,DAB},b}$
$model_{\text{sw,DAB,bat},b}$	$n_{\text{par,cap,bat},b}$	$model_{\text{wire,Tx,DAB},b}$
$model_{\text{sw,DAB,grid},b}$	$model_{\text{cap,bat},b}$	$model_{\text{wire,L,inv},b}$
$model_{\text{sw,inv},b}$	$model_{\text{cap,dclink},b}$	$n_{\text{t,L,DAB},b}$
V_{dc}	$n_{\text{core,L,DAB},b}$	$n_{\text{t,Tx,DAB,bat},b}$
$f_{\text{s,DAB},b}$	$n_{\text{core,Tx,DAB},b}$	$n_{\text{L,inv},b}$
$m_{f,b}$	$n_{\text{core,L,inv},b}$	$npw_{\text{L,DAB},b}$
$model_{\text{HS,DAB,bat},b}$	$model_{\text{core,L,DAB},b}$	$npw_{\text{Tx,DAB,bat},b}$
$model_{\text{HS,DAB,grid},b}$	$model_{\text{core,Tx,DAB},b}$	$npw_{\text{Tx,DAB,grid},b}$
$model_{\text{HS,inv},b}$	$model_{\text{core,L,inv},b}$	$npw_{\text{L,inv},b}$

- 76 optimization variables
- All variables are discrete

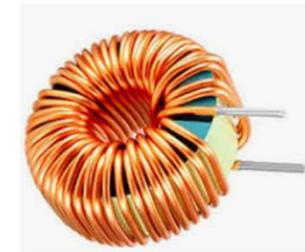
Design Space

Opt. variable	Design space
$n_{\text{par,sw,DAB,bat,b}}$	3, 4
$n_{\text{par,sw,DAB,grid,b}}$	Up to 2
$n_{\text{par,sw,inv,b}}$	Up to 2
$\text{type}_{\text{sw,DAB,bat,LTO}}$	Discrete Si MOSFET, Discrete SiC MOSFET
$\text{model}_{\text{sw,DAB,bat,b}}$	<u>LTO battery:</u>
	<ul style="list-style-type: none"> - Si MOSFET: IRF100P218, IRF100P219, IPP023N10N5, IPP030N10N5, STF150N10F7, IPB120N10S4-03, SUP70090E, IPD122N10N3G, IPP126N10N3G - SiC MOSFET: UF3SC065007K4S
$\text{model}_{\text{sw,DAB,grid,b}}$	<u>AORF battery:</u>
	<ul style="list-style-type: none"> - Si MOSFET: SiHG018N60E, SiHG026N60EF, IPZ60R017C7, IPW60R017C7, IPW60R018CFD7, IPW60R024CFD7, IPW60R024P7, IPZA60R024P7, IPW60R041P6, IPW60R060P7
$\text{model}_{\text{sw,DAB,inv,b}}$	SiC MOSFET modules: CAB006M12GM3, CAB008M12GM3, CCB032M12FM3
V_{dc}	700 V, 750 V, 800 V
$f_{\text{s,DAB,b}}$	20 kHz, 24 kHz, ..., 92 kHz, 96 kHz, 100 kHz
$m_{\text{f,b}}$	201, 219, 237, ..., 687, 705, 723
$\text{model}_{\text{HS,DAB,bat,b}}$	From Advanced Thermal Solutions extrusion heat sinks catalogue:
$\text{model}_{\text{HS,DAB,grid,b}}$	<ul style="list-style-type: none"> - ATS-EXL6, ATS-EXL59, ATS-EXL64, ATS-EXL66, ATS-EXL67, ATS-EXL75
$\text{model}_{\text{HS,inv,b}}$	



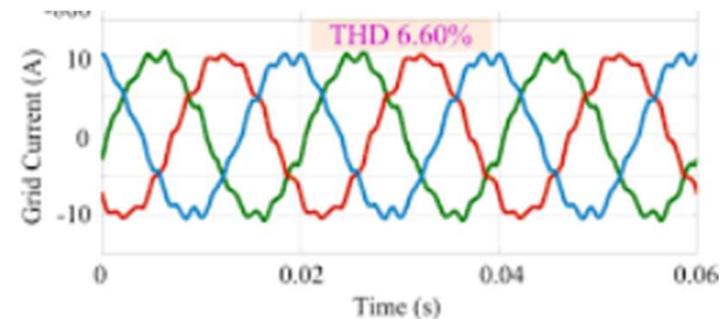
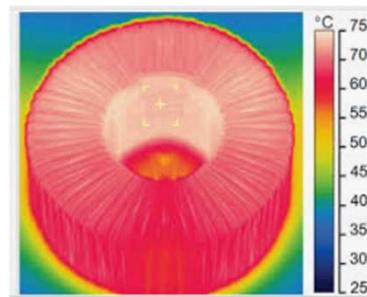
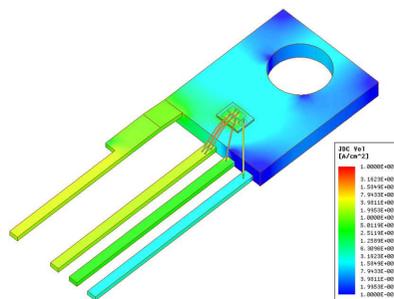
Design Space

Opt. Variable	Design space
$model_{cap,bat,b}$	From Cornell Dubilier Electronics film capacitors:
$model_{cap,dclink,b}$	947D152K901DLRSN, 947C102K901DCHS, 947D112K102DLRSN, 947C641K102DBHS, 947C321K122DAHS, 944U101K122AC, 944U660K102AA
$n_{core,L,DAB,b}$	1 to 5
$n_{core,Tx,DAB,b}$	1 to 5
$n_{core,L,inv,b}$	1 to 5
$model_{core,L,DAB,b}$	From Magnetics cores catalogue: 0077169A7, 0077101A7, 0077336A7, 0059188A2, 0059909A2
$model_{core,Tx,DAB,b}$	From Magnetics cores catalogue: 00K114LE014, 0077164A7, 0077169A7, 0077101A7, 0077614A7, 0077336A7, 0077869A7, 0077740A7, 0077778A7
$model_{core,L,inv,b}$	From Magnetics and TDK Electronics cores catalogue: E32/16/11 (Ferrite), 00K3112U090, 00K114LE014, 0077164A7, 0077169A7, 0077101A7, 0077614A7, 0077336A7, 0077869A7
$type_{wire,L,DAB,b}$	Round, Foil, Litz
$type_{wire,Tx,DAB,b}$	Round, Foil, Litz
$type_{wire,L,inv,b}$	Round, Foil, Litz
$model_{wire,L,DAB,b}$	- Round wires: 2 AWG to 30 AWG
$model_{wire,Tx,DAB,b}$	- Litz wires: from $\varnothing 0.04\text{mm}$ strand and 45 conductors per litz, to $\varnothing 0.28\text{mm}$ strand and 1350 conductors per litz
$n_{t,L,DAB,b}$	Up to 25 turns
$n_{t,Tx,DAB,bat,b}$	Up to 18 turns
$n_{L,inv,b}$	Up to 30 turns



Constraints

- ❑ Semiconductors max. temperature < 120 °C
- ❑ Magnetics max. temperature < 100 °C
- ❑ Magnetics max. flux density < B_{sat} value from datasheet.
- ❑ Grid current THD < 10 %
- ❑ dc-link voltage ripple < 10 %
- ❑ ...other constraints related to the converters modulation.



Optimization Problem Solving

$$\min_{\mathbf{y}} G_{x,w}(\mathbf{y}) = W_{\zeta_w} \cdot \zeta'_{x,w}(\mathbf{y}) + W_{\sigma_w} \cdot \sigma'_{x,w}(\mathbf{y})$$

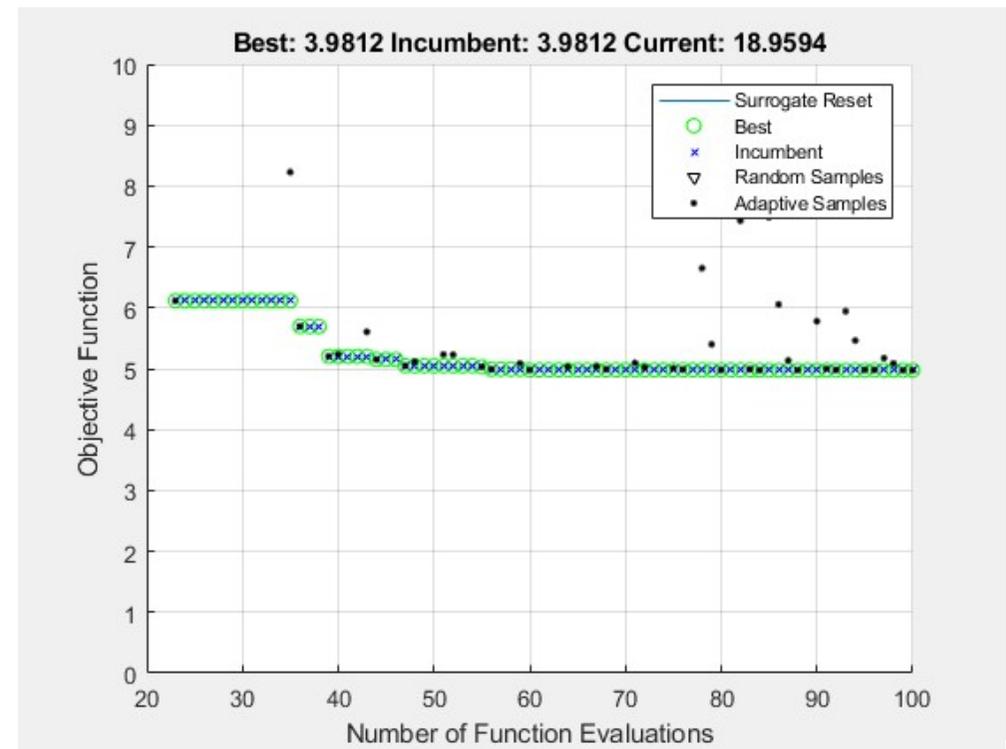
subject to constraints:

$$y_i \in \mathbb{Z}, \quad i = 1, \dots, 76$$

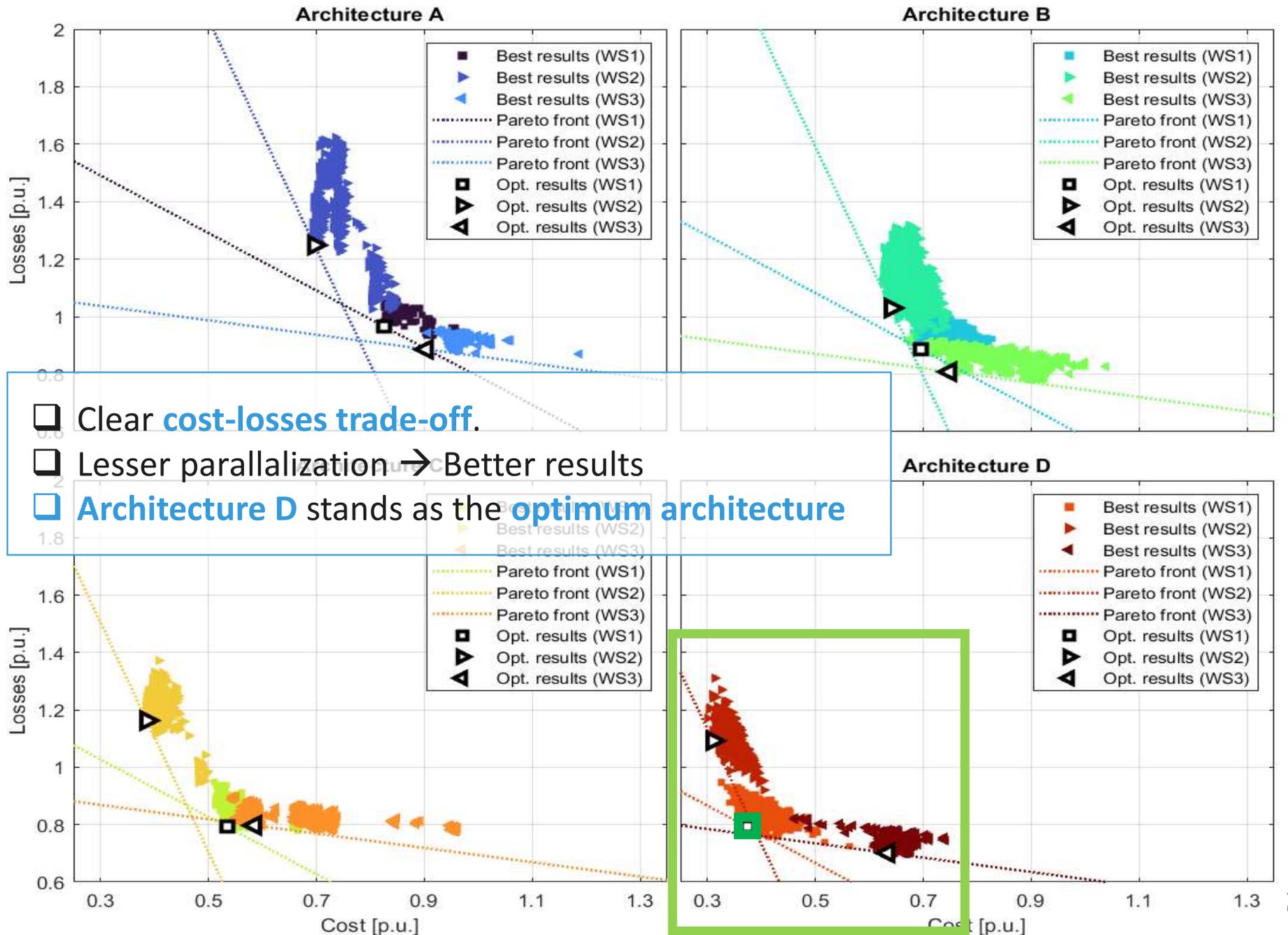
$$l_{b,i} \leq y_i \leq u_{b,i}, \quad l_{b,i}, u_{b,i} \in \mathbb{Z}.$$

Solved with **MATLAB Surrogate** optimization algorithm.

Executed 6x times per architecture (x4) and weight set (x3) = 76 Executions.



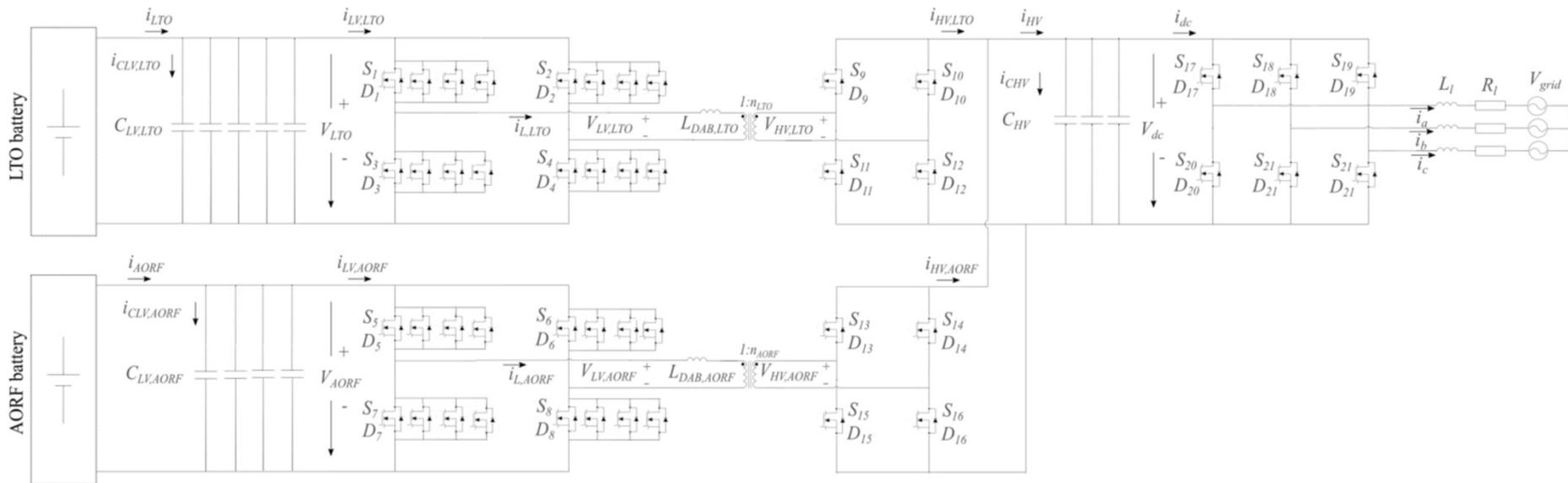
Optimization results



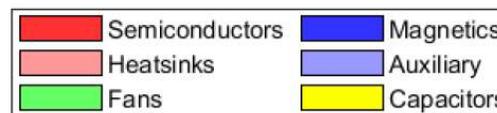
- ☐ Clear **cost-losses trade-off**.
- ☐ Lesser parallelization → Better results
- ☐ **Architecture D** stands as the **optimum architecture**

Optimization results

□ **WS1 Arch. D** design is selected for its competitive cost-losses trade-off.



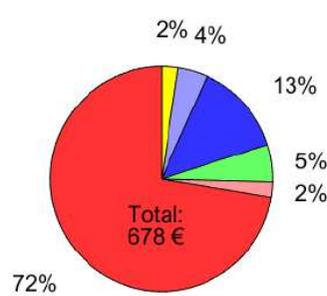
Share of capital cost



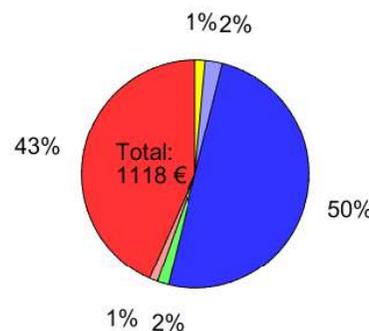
LTO DAB converter



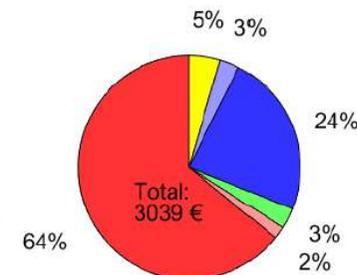
AORF DAB converter



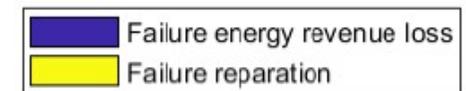
dc-ac converter



Power system



Share of reliability cost



Conclusion

We have developed an **Electronic Design Automation tool** with comprehensive and **multiphysics modelling** to:

- ❑ Obtain a set of power converter designs with **optimum performance** offering a **wide range** of **cost-losses trade-off**.
- ❑ The converter design are defined to the component level → **Ready-to-go for converter implementation**.

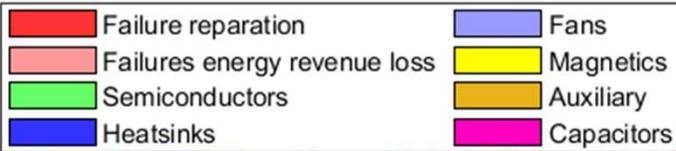
In HYBRIS context: Architectures with lower degree of parallelization offer the performance:

- ❑ However, if reliability cost is accounted for a longer period, these Architectures may not become cost competitive.

THANK YOU FOR YOUR ATTENTION



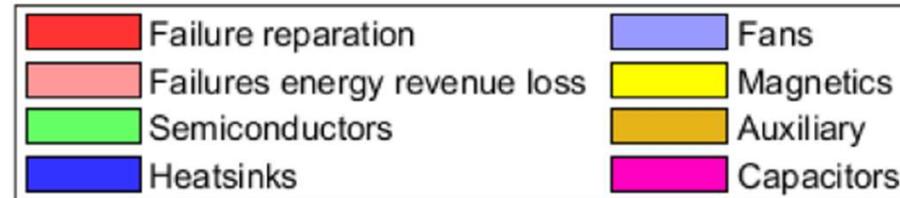
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Optimization results



of the
Optimum solutions



	Architecture A	Architecture B	Architecture C	Architecture D
WS1	<p>Total cost: 8247 € 71%</p>	<p>Total cost: 6944 € 64%</p>	<p>Total cost: 5352 € 67%</p>	<p>Total cost: 3735 € 52%</p>
WS2	<p>Total cost: 6963 € 69%</p>	<p>Total cost: 6404 € 64%</p>	<p>Total cost: 3854 € 61%</p>	<p>Total cost: 3100 € 52%</p>
WS3	<p>Total cost: 9037 € 73%</p>	<p>Total cost: 7491 € 65%</p>	<p>Total cost: 5854 € 70%</p>	<p>Total cost: 6344 € 66%</p>